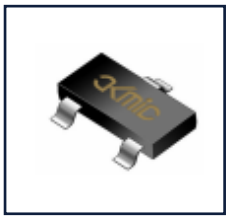
General Features

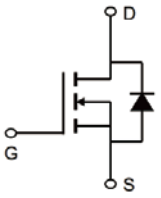
- V_{DS} = -20V I_D =-3A
- $R_{DS(ON)}$ < 55mΩ @ V_{GS}=-4.5V



SOT23

Applications

- Battery protection
- Load switch
- Uninterruptible power supply



Equivalent Circuit

Description

The DMP2120U-7 uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

Ordering information

Product ID	Pack	Marking	Qty(PCS)
DMP2120U-7	SOT23	A1SHB S1	3000

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D@T_A=25℃	Continuous Drain Current, VGS @ 4.5V1	-3	A
I_D@T_A=70℃	Continuous Drain Current, VGS @ 4.5V1	-2.6	A
I_{DM}	Pulsed Drain Current2	-13	A
P_D@T_A=25℃	Total Power Dissipation3	1.4	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
$R_{\theta JA}$	Thermal Resistance Junction-ambient 1	125	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case1	90	℃/W

Electrical Characteristics (T_A=25℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-20	-22	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance2	V_{GS}=-4.5V , I_D=-3A	---	55	80	mΩ
		V_{GS}=-2.5V , I_D=-2A	---	75	100	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-0.45	-0.6	-1.0	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-20V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-20V , V_{GS}=0V , T_J=55℃	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±12V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-3A	---	12.2	---	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	677	---	pF
C_{oss}	Output Capacitance		---	82	---	
C_{rss}	Reverse Transfer Capacitance		---	73	---	
Q_g	Total Gate Charge (4.5V)	V_{DS}=15V , V_{GS}=-4.5V , I_D=-3A	---	10.1	---	nC
Q_{gs}	Gate-Source Charge		---	1.21	---	
Q_{gd}	Gate-Drain Charge		---	2.46	---	
Switching Characteristics						
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-10V , V_{GS}=-4.5V , R_G=3.3Ω I_D=3A	---	5.6	---	ns
T_r	Rise Time		---	32.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	45.6	---	
T_f	Fall Time		---	29.2	---	
Drain-Source Diode Characteristics and Maximum Ratings						
IS	Continuous Source Current1,4	V_G=V_D=0V , Force Current	---	---	-3	A
VSD	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1	V

Note :

1、The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width △ 300us , duty cycle △ 2%

3、The power dissipation is limited by 150℃ junction temperature

4、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

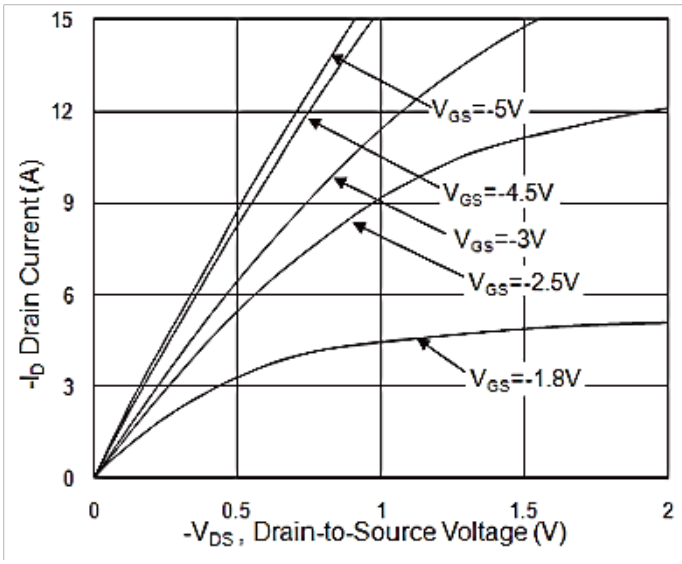


Fig.1 Typical Output Characteristics

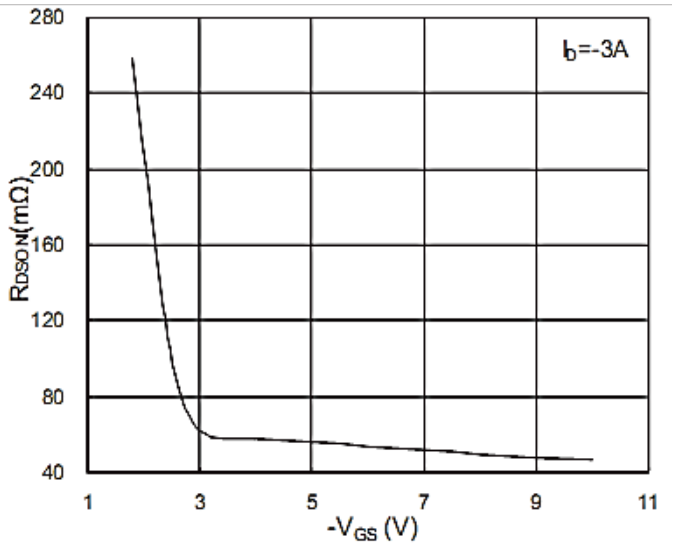


Fig.2 On.Resistance vs. G.S Voltage

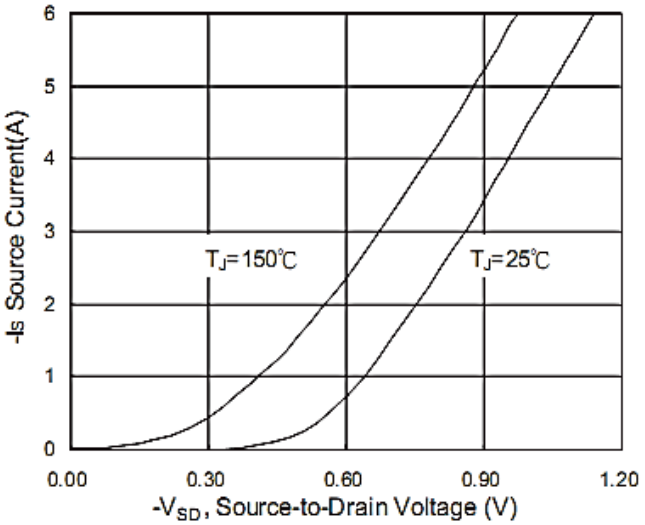


Fig.3 Forward Characteristics Of Reverse

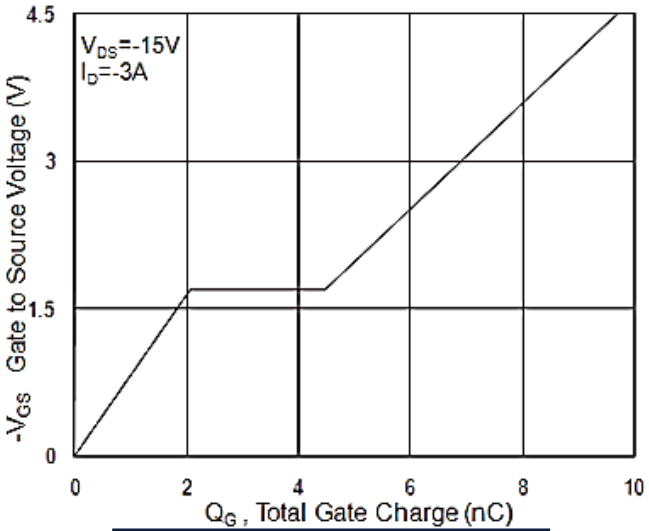


Fig.4 Gate-Charge Characteristics

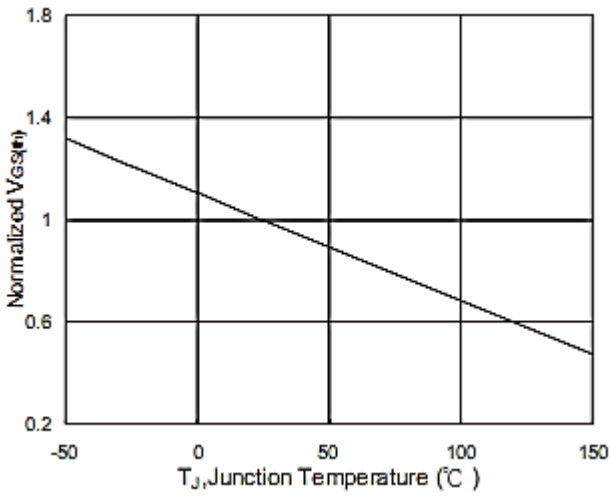


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

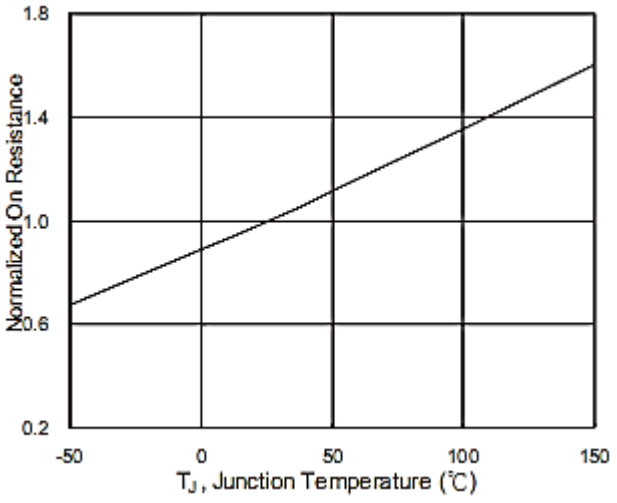


Fig.6 Normalized R_{DSON} vs. T_J

Typical Characteristics

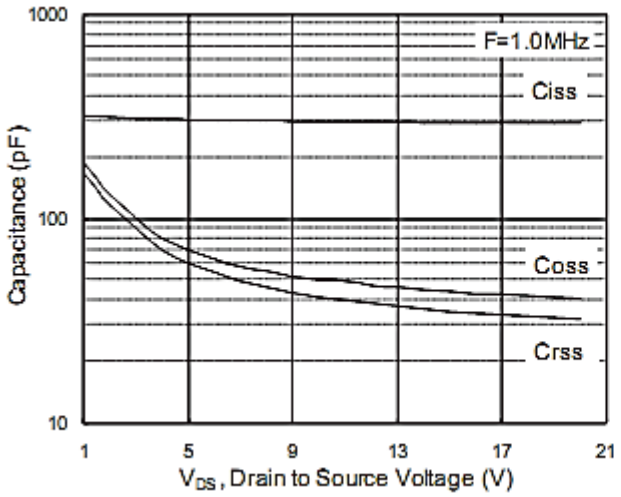


Fig.7 Capacitance

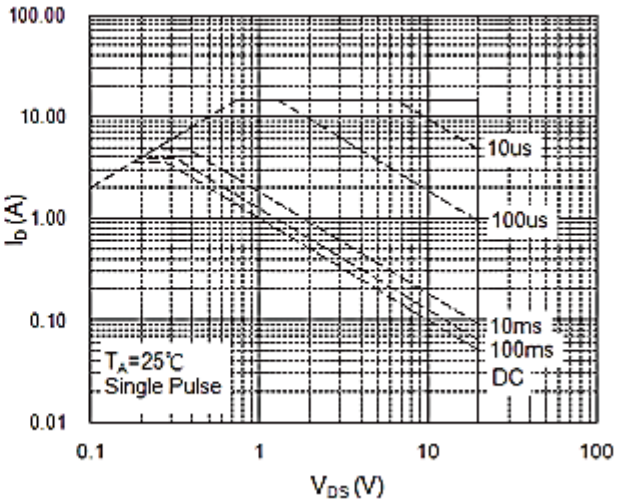


Fig.8 Safe Operating Area

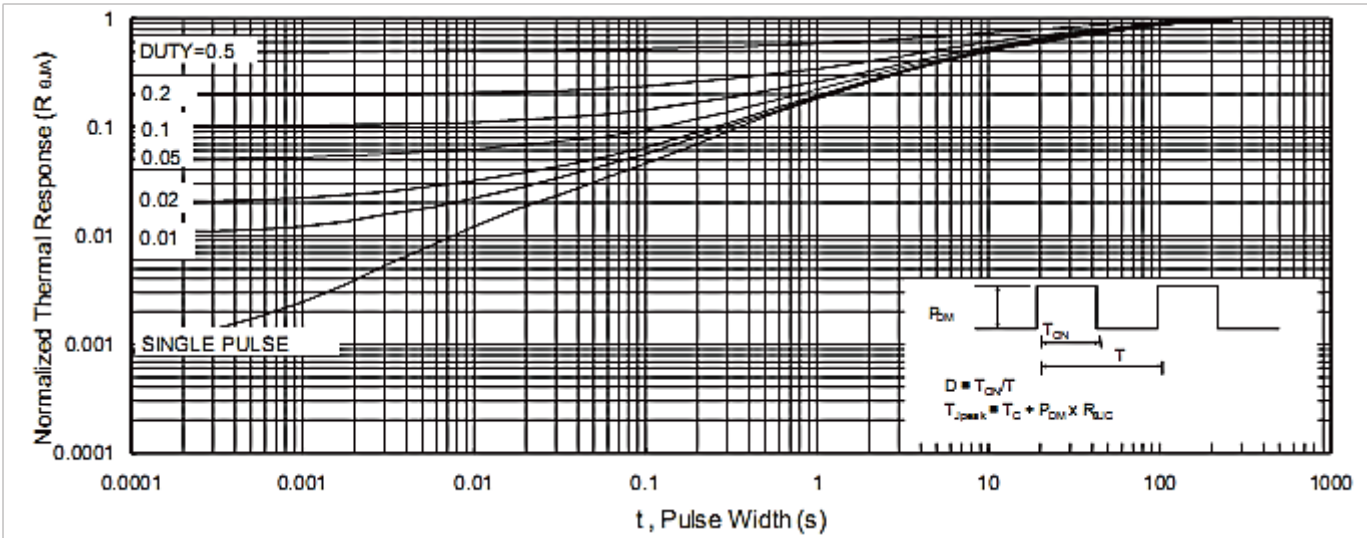


Fig.9 Normalized Maximum Transient Thermal Impedance

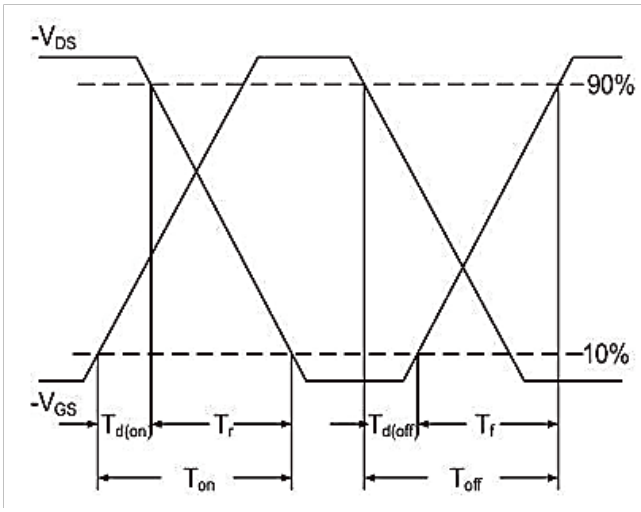


Fig.10 Switching Time Waveform

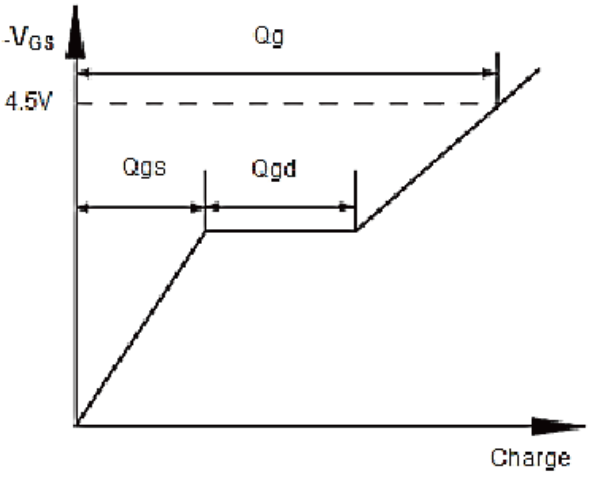
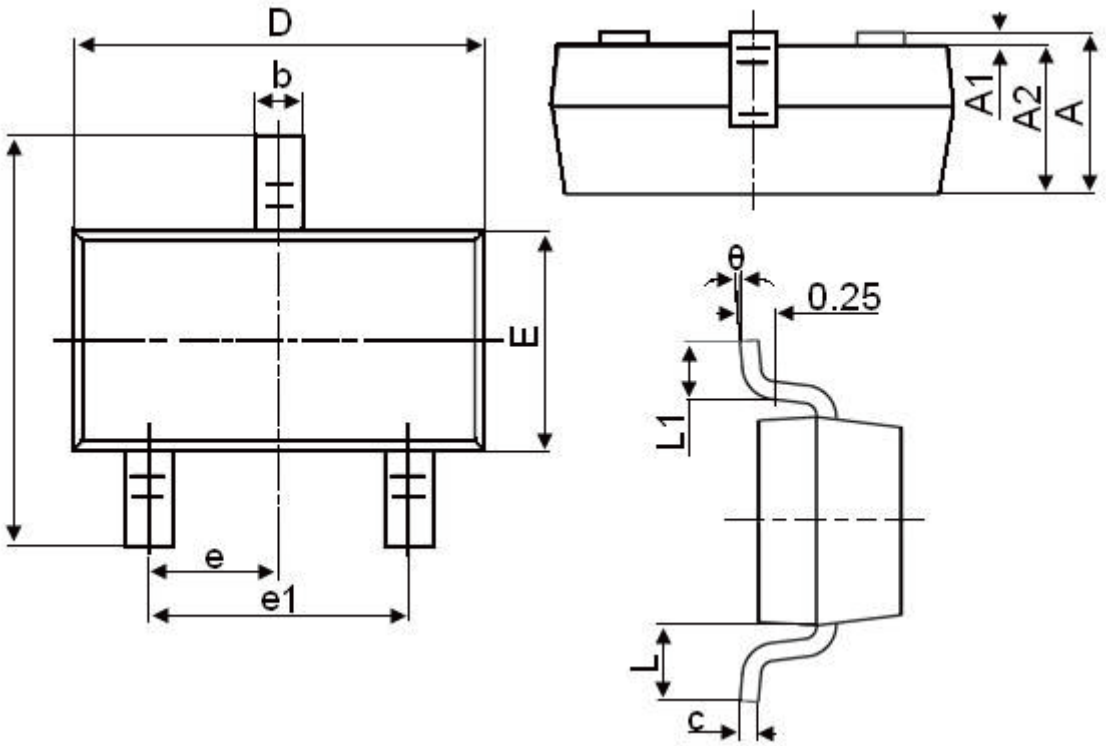


Fig.11 Gate Charge Waveform

SOT23 Package Outline Dimensions



Symbol	Dimensions in Millimeters	
	mm	
	Min	Max
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°